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Buck chopper MOSFET Power Module

Q1

G1

() S1

G

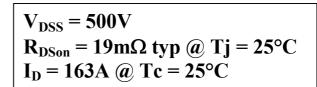
VBUS

OUT

0/VBUS

CR2

0/VBUS



Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Power MOS 7[®] MOSFETs
- Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		500	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	163	
I _D		$T_c = 80^{\circ}C$	122	А
I _{DM}	Pulsed Drain current	652		
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		22.5	mΩ
P _D	Maximum Power Dissipation $T_c = 25^{\circ}C$		1136	W
I _{AR}	Avalanche current (repetitive and non repetitive)		46	А
E _{AR}	Repetitive Avalanche Energy		50	mJ
E _{AS}	Single Pulse Avalanche Energy	e Avalanche Energy		IIIJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$	$T_j = 25^{\circ}C$			200	μA
		$V_{GS} = 0V, V_{DS} = 400V$	$T_j = 125^{\circ}C$			1000	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 81.5A$			19	22.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10 \text{mA}$		3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$				±200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		22.4		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		4.8		nF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		0.36		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		492		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		132		nC
Q_{gd}	Gate – Drain Charge	$I_{\rm D} = 163 \rm A$		260		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 163A$ $R_G = 1\Omega$		18		ns
T _r	Rise Time			35		
T _{d(off)}	Turn-off Delay Time			87		
T_{f}	Fall Time			77		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 163A, R_G = 1\Omega$		3020		
E _{off}	Turn-off Switching Energy			2904		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$, $V_{Bus} = 333V$ $I_D = 163A$, $R_G = 1\Omega$		4964		т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			3384		μJ

Chopper diode ratings and characteristics

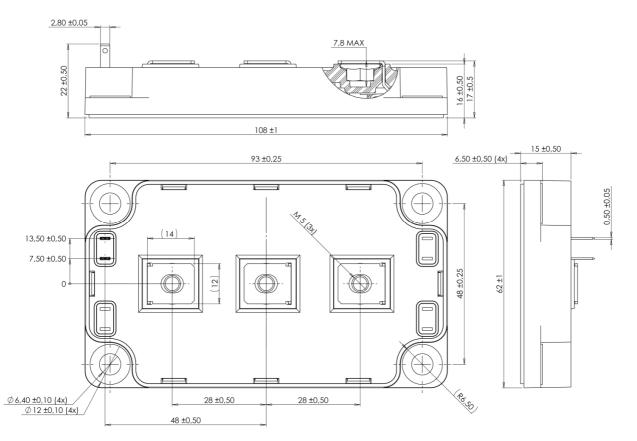
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$			350 600	μΑ
$I_{\rm F}$	DC Forward Current		$T_c = 70^{\circ}C$		120		А
	Diode Forward Voltage	$I_{\rm F} = 120 {\rm A}$			1.6	1.8	
$V_{\rm F}$		$I_F = 240A$			1.9		V
		$I_{\rm F} = 120 {\rm A}$	$T_{j} = 125^{\circ}C$		1.4		
t _{rr}	Reverse Recovery Time $I = 120 \Lambda$	$I_{\rm F} = 120 A$ $V_{\rm P} = 400 V$	$T_j = 25^{\circ}C$		130		ns
۲r			$T_j = 125^{\circ}C$		170		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 400 \text{A}/\mu\text{s}$	$T_j = 25^{\circ}C$		440		nC
Qrr			$T_j = 125^{\circ}C$		1840		ne



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance Transiste Diode		Transistor			0.11	°C/W
R _{thJC}			Diode			0.46	C/ W
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

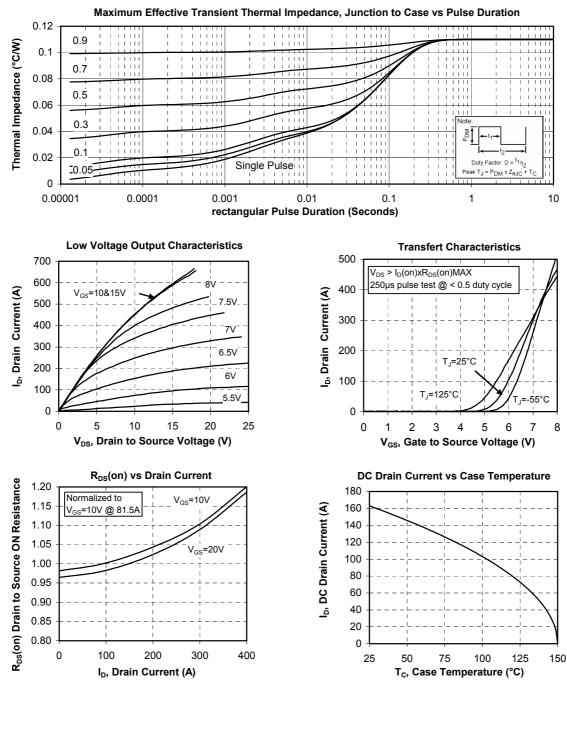
SP6 Package outline (dimensions in mm)



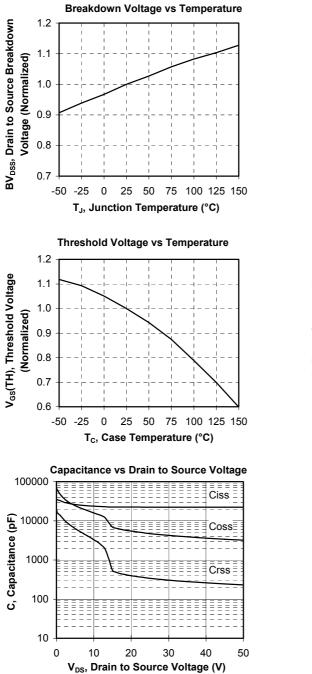
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

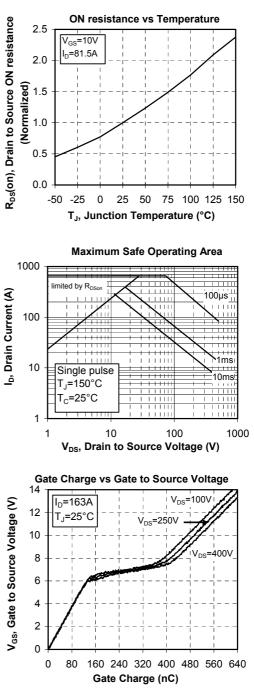


Typical Performance Curve











150

100

50

0

0 20

D=50%

R_G=1Ω

T_J=125°C

T_C=75°C

40 60 80

Hard

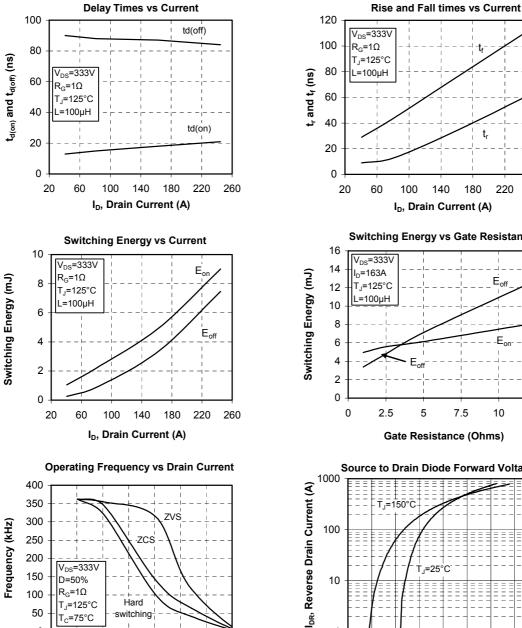
witching

I_D, Drain Current (A)

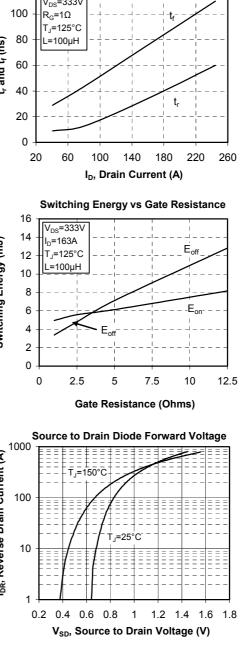
100

120

140



APTM50SKM19G





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